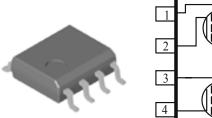
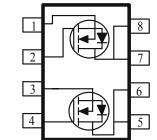
### **Dual N-Channel 30-V (D-S) MOSFET**

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	V) $r_{DS(on)} m(\Omega)$ $I_D (A$			
30	$58 @ V_{GS} = 4.5V$	5.0		
	82	4.2		

- $\begin{array}{ll} \bullet & \quad Low \; r_{DS(on)} \; provides \; higher \; efficiency \; and \\ extends \; battery \; life \\ \end{array}$
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			30	V		
Gate-Source Voltage		$V_{GS}$	± 12	V		
C t D c C t <sup>a</sup>	$T_A=25^{\circ}C$		5.0			
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	4.1	Α		
Pulsed Drain Current <sup>b</sup>			± 30			
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	1.7	A		
D	$T_A=25^{\circ}C$	D	2.1	W		
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	$P_{\rm D}$	1.3			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
M . I	t <= 10 sec	D	62.5	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	$R_{ heta JA}$	80	°C/W		

1

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

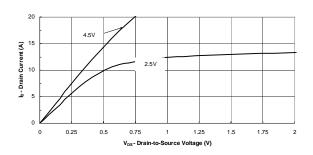
Parameter	Symbol	Test Conditions	Limits			Unit	
r ar ameter	Symbol Test Conditions		Min	Тур	Max	Omt	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	0.7				
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Carrent	-1033	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	ur i	
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	20			A	
Drain-Source On-Resistance <sup>A</sup>		$V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$			58	mΩ	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 4.2 \text{ A}$			82	11122	
Forward Tranconductance <sup>A</sup>	$\mathbf{g}_{\mathrm{fs}}$	$V_{DS} = 15 \text{ V}, I_D = 5 \text{ A}$		22		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 1.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{g}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		6.3			
Gate-Source Charge	$Q_{gs}$	$V_{DS} - 13 V, V_{GS} - 4.3 V,$ $I_{D} = 5 A$		0.9		nC	
Gate-Drain Charge	$Q_{gd}$			1.9			
Input Capacitance	$C_{iss}$			257			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{MHz}$		62		pF	
Reverse Transfer Capacitance	$C_{rss}$			30			
Turn-On Delay Time	$t_{d(on)}$			22			
Rise Time	$t_{\rm r}$	$V_{DD} = 15 \text{ V}, R_L = 15 \Omega, I_D = 1 \text{ A},$		40		nS	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}$		50		113	
Fall-Time	$t_{\mathrm{f}}$			20		1	

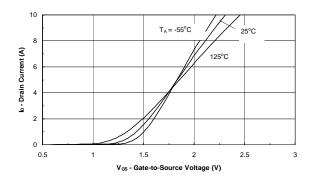
#### Notes

- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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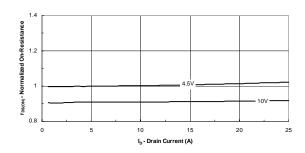
## Typical Electrical Characteristics (N-Channel)

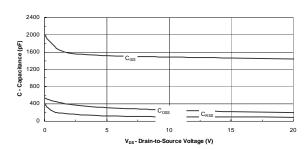




#### **Output Characteristics**

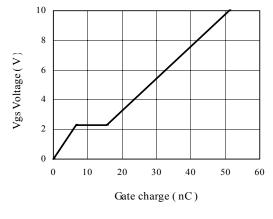
**Transfer Characteristics** 

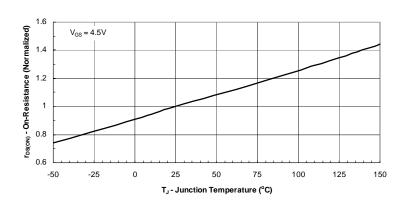




#### On-Resistance vs. Drain Current

Capacitance





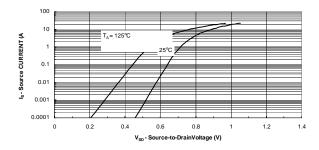
Gate Charge

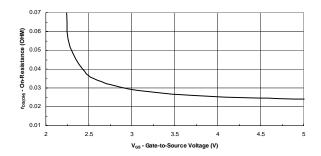
On-Resistance vs. Junction Temperature

-50

-25

## Typical Electrical Characteristics (N-Channel)

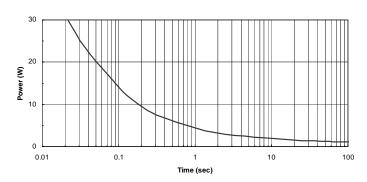


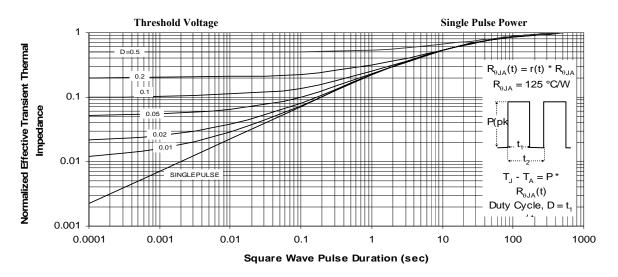


#### Source-Drain Diode Forward Voltage

T<sub>1</sub> - Temperature (°C)

#### On-Resistance vs.Gate-to Source Voltage

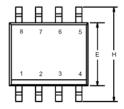


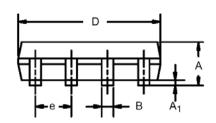


Normalized Thermal Transient Impedance, Junction-to-Ambient

# Package Information

SO-8: 8LEAD





	MILLIMETERS		INC	HES
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
В	0.35	0.51	0.014	0.020
С	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

